

Caroline Chèze received her PhD in Experimental Physics in 2010 from the Humboldt University in Berlin under the supervision of Prof. Dr. H. Riechert. Her thesis was focused on the Investigation of GaN nanowire Nucleation and Growth by Plasma-Assisted Molecular Beam Epitaxy (PAMBE). At the end of 2010, she joined the group of Prof. Dr. C. Skierbiszewski at the Company TopGaN Lasers / Institute of High Pressure Physics in Warsaw where she worked as a postdoctoral researcher within the Marie Skłodowska-Curie project SINOPLE (“Surface engineered InGaN heterostructures on N-polar and nonpolar GaN-substrates for green light emitters”) on the fabrication and characterization of planar N-polar (000 $\bar{1}$) (Al,In,Ga)N heterostructures. At the beginning of 2013 she joined the group of PD Dr. R. Calarco at the Paul-Drude-Institut für Festkörperelektronik in Berlin. She is involved in the ITN project SPRInG (“Short Period Superlattices for Rational (In,Ga)N”) as Work-Package leader for the Epitaxy activity. Her research interests are focused on the epitaxy of III-nitride heterostructures in the shape of layers and nanostructures.